

Abstract of The Disclosure

With a high-speed nonvolatile phase change memory, reliability in respect of the number of refresh times is enhanced.

In a memory cell forming area of a phase change memory using

5 a MISFET as a transistor for selection of memory cells, a phase

change material layer of a memory cell comprising a resistor

element, using a phase change material, is formed for common

use. As a result, variation in shape and a change in composition

of the phase change material, caused by isolation of memory cell

10 elements by etching, are reduced, thereby enhancing reliability

of memory cells, in respect of the number of refresh times.